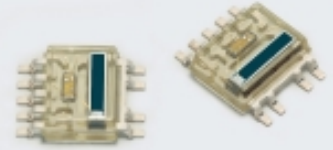


# Photo IC for laser beam synchronous detection

## S10317 series

### Low voltage operation (3.3 V)



S10317 series photo IC uses a high-speed PIN photodiode designed for laser beam synchronous detection. S10317 series is driven by a low voltage (3.3 V) compatible with low voltage peripheral components that will be mounted on the same PC board. Two types of current amplifiers are available with a gain of 6 times (S10317-01) and 20 times (S10317) that can be selected according to laser power to be used. Tape-and-reel shipment is also available (S10317-30 and S10317-31).

#### Features

- Low voltage operation (3.3 V)
- High sensitivity  
Current amplifier gain: 20 times (S10317)  
6 times (S10317-01)
- Digital output
- Small package
- Suitable for lead-free solder reflow
- Active area: 2.84 × 0.5 mm

#### Applications

- Print start timing detection for laser printers, digital copiers, fax machines, etc.

#### ■ Absolute maximum ratings (Ta=25 °C, unless otherwise noted)

Parameter	Symbol	Value	Unit
Supply voltage	Vcc	-0.5 to +7	V
Power dissipation *1	P	300	mW
Output voltage *2	Vo	-0.5 to +7	V
Output current	Io	5	mA
Ro terminal current	IRO	3	mA
Operating temperature	Topr	-25 to +80	°C
Storage temperature	Tstg	-40 to +85	°C

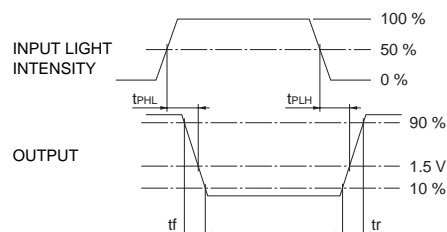
\*1: Power dissipation decreases at a rate of 4 mW/°C above Ta=25 °C.

\*2: Vcc=+0.5 V or less

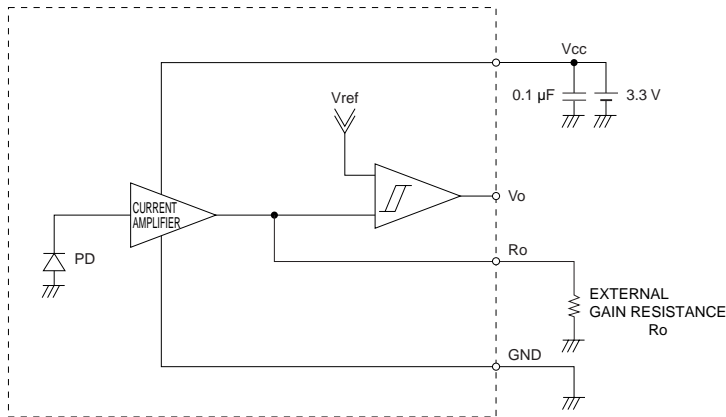
#### ■ Electrical and optical characteristics (Ta=25 °C, λ=780 nm, Vcc=3.3 V, Ro=5.1 kΩ, unless otherwise noted)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	
Current consumption	Icc	No input	-	0.7	1.5	mA	
High level output voltage	VOH	IOH=4 mA	2.9	-	-	V	
Low level output voltage	VOL	IOL=4 mA *3	-	-	0.3	V	
Threshold input power	S10317	PTH	14	19	24	μW	
	S10317-01		49.5	62	74.5		
H L propagation delay time	S10317	Pi=57 μW (S10317) Pi=186 μW (S10317-01) Duty ratio 1:1 CL=15 pF *4	-	130	250	ns	
	S10317-01		tPHL	-	100		200
L H propagation delay time	S10317		tPLH	-	200		300
	S10317-01		tPLH	-	150		250
Rise time	tr		-	4	7	ns	
Fall time	tf		-	4	7	ns	
Maximum input power	PI Max.		-	-	PTH × 8	μW	

\*3: Input power [Pi]=57 μW (S10317), Pi=186 μW (S10317-01)



■ Block diagram



KPIC0127EA

■ Function

S10317 series photo IC integrates a photodiode chip and an IC chip into the same package. The photodiode chip is internally connected to the IC chip as shown in the block diagram. S10317 series should be used with terminal Ro connected to an external gain resistance Ro.

A photocurrent is generated when a laser beam enters the photodiode. This photocurrent is fed to the input terminal of the IC and, after being amplified by the current amplifier, flows to the external gain resistance. At this time, voltages VRO at terminal Ro is given by the following expression.

$$V_{RO} = A \times S \times P_i \times R_o \text{ [V]} \dots\dots\dots (1)$$

A: Current amplifier gain (S10317: 20 times, S10317-01: 6 times)

S: Photodiode sensitivity [A/W] (approx. 0.44 A/W at 780 nm)

Pi: Input power [W]

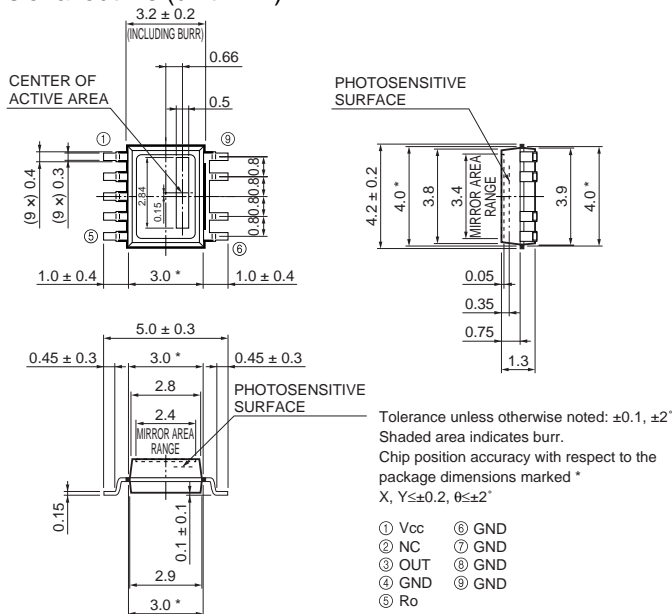
Ro: External gain resistance [Ω]; usable range 2 kΩ to 10 kΩ

VRO is input to the internal comparator and compared with the internal reference voltage Vref (approx. 0.8 V) so the output Vo is "High" when VRO < Vref or "Low" when VRO > Vref.

In equatin (1), set the Ro value so that VRO is 2 to 3 V.

(Monitoring VRO shows that it is limited to about 2 V (with respect to GND) by the voltage limiting circuit. Keep this in mind when monitoring.)

■ Dimensional outline (unit: mm)



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